Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

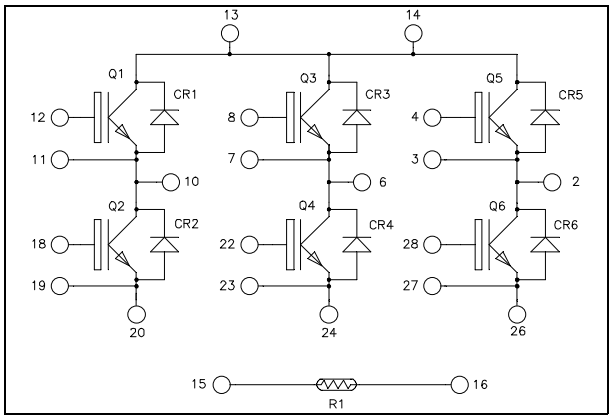
Contact us

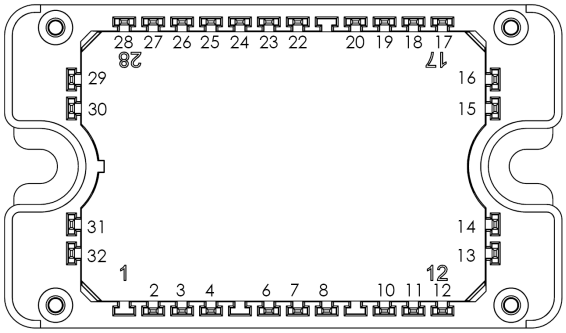
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

APTGTQ50TA65T3G

Triple phase leg
High speed IGBT 5 Power Module

V_{CES} = 650V ; I_C = 50A @ Tc = 25°C





Pins 20, 24 & 26 must be shorted together to perform a 3 phase bridge.

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- High speed IGBT 5
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 100 kHz
  - Low leakage current
- Very low stray inductance
- Kelvin source for easy drive
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Voltage		650	V
I_C	Continuous Collector Current	T_C = 25°C	50	A
		T_C = 80°C	30	
I_{CM}	Pulsed Collector Current	T_C = 25°C	100	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Power Dissipation		125	W

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handing Procedures Should Be Followed.

Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 650V				50	µA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} =15V I_C = 50A	T_j = 25°C		1.65	2.2	V
			T_j = 150°C		1.9		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 0.5mA		3.3	4.0	4.7	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				120	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			3000		pF
C_{oes}	Output Capacitance				50		
C_{res}	Reverse Transfer Capacitance				11		
Q_G	Gate charge	V_{GE} = 15V, I_C = 50A V_{CE} = 520V			120		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = 15V V_{Bus} = 400V I_C = 25A R_G = 12Ω			21		ns
T_r	Rise Time				15		
$T_{d(off)}$	Turn-off Delay Time				180		
T_f	Fall Time				18		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) V_{GE} = 15V V_{Bus} = 400V I_C = 25A R_G = 12Ω			20		ns
T_r	Rise Time				15		
$T_{d(off)}$	Turn-off Delay Time				205		
T_f	Fall Time				26		
E_{on}	Turn on Energy	V_{GE} = 15V V_{Bus} = 400V I_C = 25A R_G = 12Ω	T_j = 150°C		0.75		mJ
E_{off}	Turn off Energy		T_j = 150°C		0.3		
R_{thJC}	Junction to Case Thermal Resistance					1.2	°C/W

Diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					650	V
I_{RM}	Reverse Leakage Current	V_R=650V				50	µA
I_F	DC Forward Current		Tc = 25°C		50		A
V_F	Diode Forward Voltage	I_F = 50A V_{GE} = 0V	T_j = 25°C		1.6	2.2	V
			T_j = 150°C		1.65		
t_{rr}	Reverse Recovery Time	I_F = 25A V_R = 400V di/dt =1500A/µs	T_j = 25°C		46		ns
			T_j = 150°C		62		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		0.5		µC
			T_j = 150°C		1		
R_{thJC}	Junction to Case Thermal Resistance					1.4	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com).

Symbol	*Characteristic*		*Min*	*Typ*	*Max*	*Unit*
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
ΔB/B		T_C=100°C		4		%

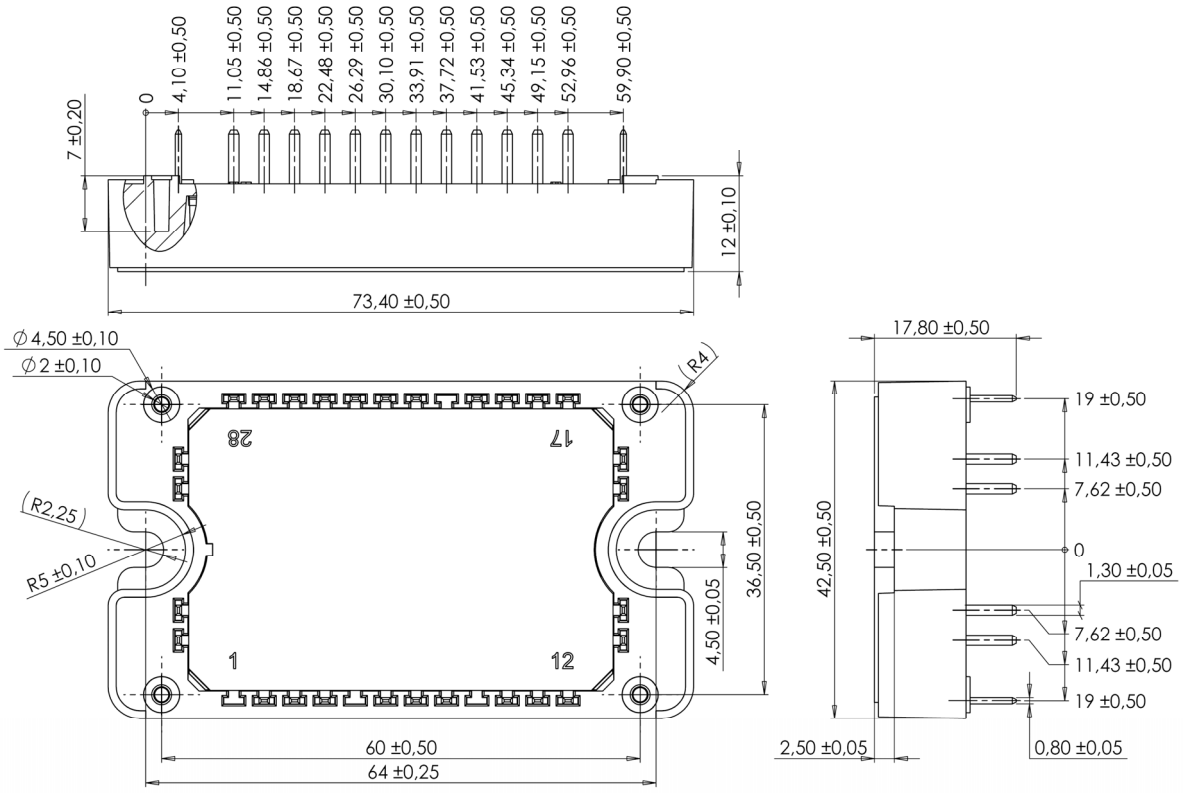
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Package characteristics

Symbol	*Characteristic*			*Min*	*Max*	*Unit*
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_J	Operating junction temperature range			-40	175	°C
T_{JOP}	Recommended junction temperature under switching conditions			-40	$T_J$max -25	
T_{STG}	Storage Temperature Range			-40	125	
T_C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

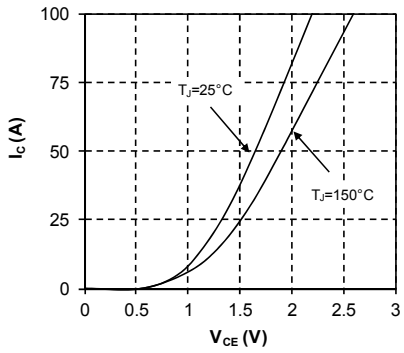
Package outline (dimensions in mm)



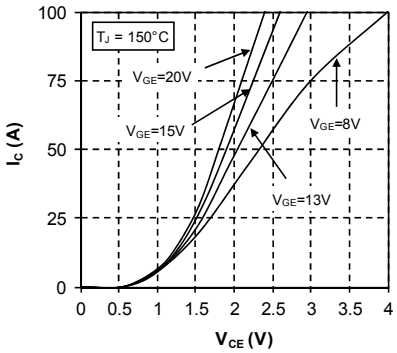
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

Typical Performance Curve

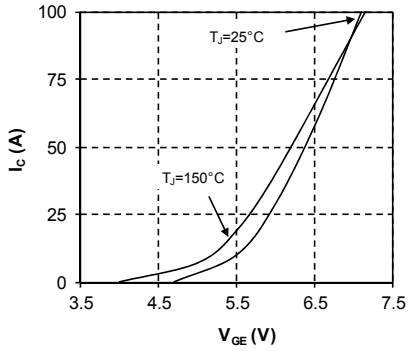
Output Characteristics (V_{GE}=15V)



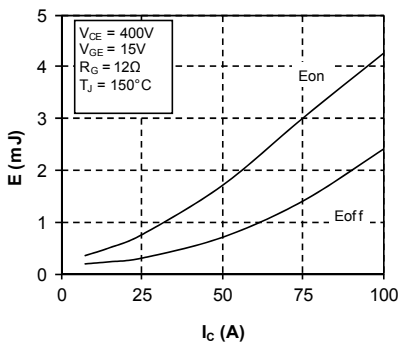
Output Characteristics



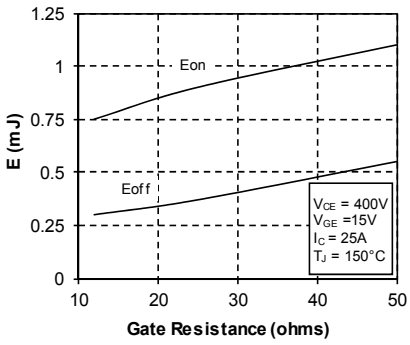
Transfert Characteristics



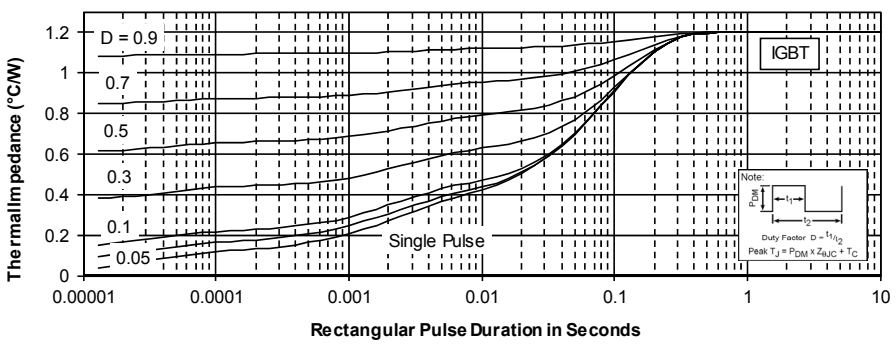
Energy losses vs Collector Current

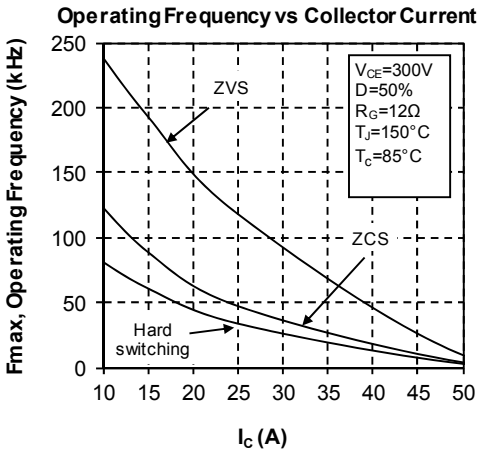


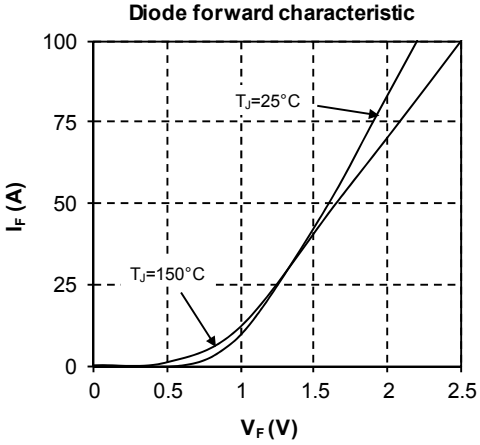
Switching Energy Losses vs Gate Resistance

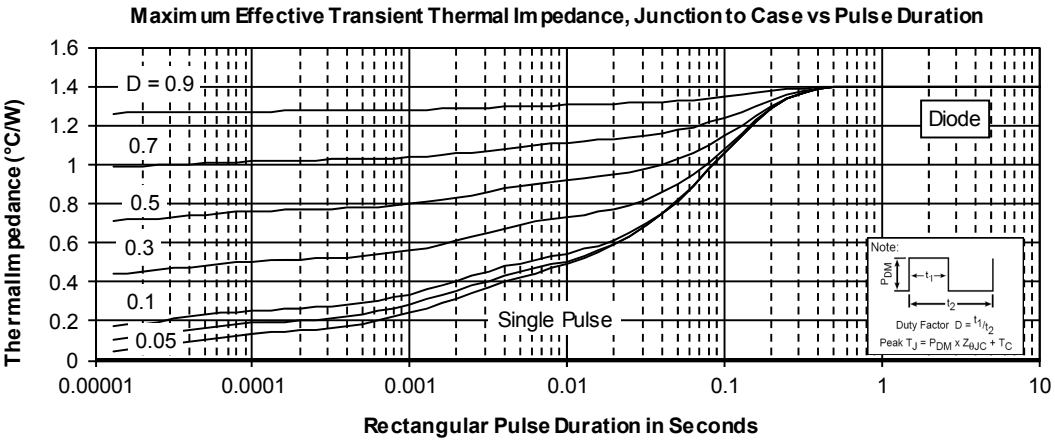


Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration




Operating Frequency vs Collector Current
Fmax, Operating Frequency (kHz)
250
200
150
100
50
0
10 15 20 25 30 35 40 45 50
I_C (A)
ZVS
ZCS
Hard switching
V_{CE}=300V
D=50%
R_G=12Ω
T_J=150°C
T_C=85°C


Diode forward characteristic
I_F (A)
100
75
50
25
0
0 0.5 1 1.5 2 2.5
V_F (V)
T_J=25°C
T_J=150°C


Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration
Thermal Impedance (°C/W)
1.6
1.4
1.2
1
0.8
0.6
0.4
0.2
0
0.00001 0.0001 0.001 0.01 0.1 1 10
Rectangular Pulse Duration in Seconds
D = 0.9
0.7
0.5
0.3
0.1
0.05
Single Pulse
Diode
Note:
Duty Factor D = t_1/t_2
Peak T_J = P_{DM} x $Z_{\theta JC}$ + T_C

DISCLAIMER

The information contained in the document (unless it is publicly available on the Web without access restrictions) is PROPRIETARY AND CONFIDENTIAL information of Microsemi and cannot be copied, published, uploaded, posted, transmitted, distributed or disclosed or used without the express duly signed written consent of Microsemi. If the recipient of this document has entered into a disclosure agreement with Microsemi, then the terms of such Agreement will also apply. This document and the information contained herein may not be modified, by any person other than authorized personnel of Microsemi. No license under any patent, copyright, trade secret or other intellectual property right is granted to or conferred upon you by disclosure or delivery of the information, either expressly, by implication, inducement, estoppels or otherwise. Any license under such intellectual property rights must be approved by Microsemi in writing signed by an officer of Microsemi.

Microsemi reserves the right to change the configuration, functionality and performance of its products at anytime without any notice. This product has been subject to limited testing and should not be used in conjunction with life-support or other mission-critical equipment or applications. Microsemi assumes no liability whatsoever, and Microsemi disclaims any express or implied warranty, relating to sale and/or use of Microsemi products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright or other intellectual property right. Any performance specifications believed to be reliable but are not verified and customer or user must conduct and complete all performance and other testing of this product as well as any user or customers final application. User or customer shall not rely on any data and performance specifications or parameters provided by Microsemi. It is the customer's and user's responsibility to independently determine suitability of any Microsemi product and to test and verify the same. The information contained herein is provided "AS IS, WHERE IS" and with all faults, and the entire risk associated with such information is entirely with the User. Microsemi specifically disclaims any liability of any kind including for consequential, incidental and punitive damages as well as lost profit. The product is subject to other terms and conditions which can be located on the web at http://www.microsemi.com/legal/tnc.asp

Life Support Application

Seller's Products are not designed, intended, or authorized for use as components in systems intended for space, aviation, surgical implant into the body, in other applications intended to support or sustain life, or for any other application in which the failure of the Seller's Product could create a situation where personal injury, death or property damage or loss may occur (collectively "Life Support Applications").
Buyer agrees not to use Products in any Life Support Applications and to the extent it does it shall conduct extensive testing of the Product in such applications and further agrees to indemnify and hold Seller, and its officers, employees, subsidiaries, affiliates, agents, sales representatives and distributors harmless against all claims, costs, damages and expenses, and attorneys' fees and costs arising, directly or directly, out of any claims of personal injury, death, damage or otherwise associated with the use of the goods in Life Support Applications, even if such claim includes allegations that Seller was negligent regarding the design or manufacture of the goods.

Buyer must notify Seller in writing before using Seller's Products in Life Support Applications. Seller will study with Buyer alternative solutions to meet Buyer application specification based on Sellers sales conditions applicable for the new proposed specific part.